ABSTRACT

~~The invention relates to~~ a method of passivating a semiconductor device with two types of transistors, e.g., NMOS and PMOS transistors~~. The~~, the semiconductor device is placed in a pressurized sealed chamber and at least two different passivating gases are introduced into the chamber. ~~Since the~~ The two passivating gases can be selected to have one gas suitable for passivating PMOS transistors and the other gas suitable for NMOS transistors~~, the method of the present invention can achieve a better result for both the NMOS and PMOS transistors~~.

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